

# **How Much Can Data Compressibility Help to Improve NAND Flash Memory Lifetime?**

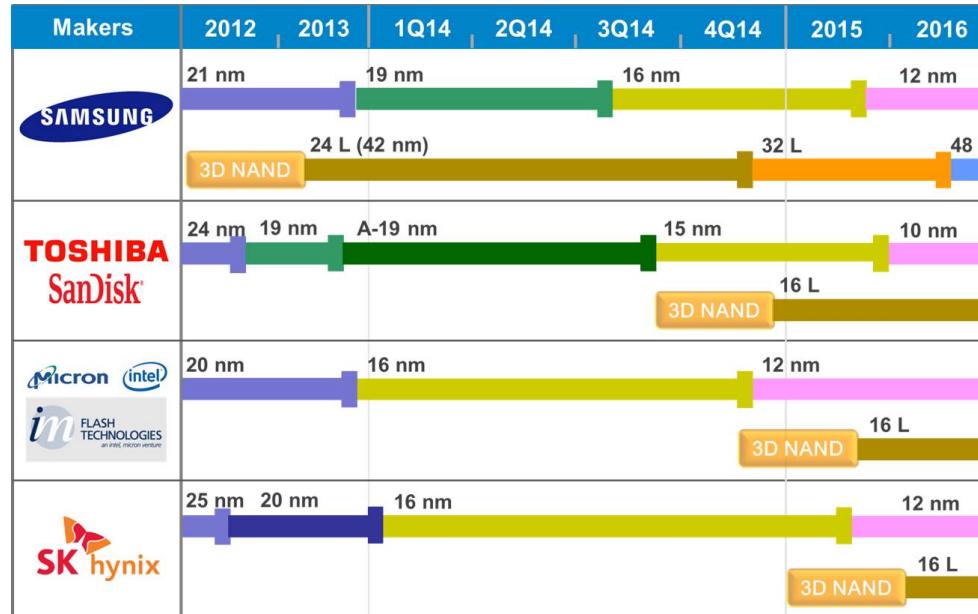
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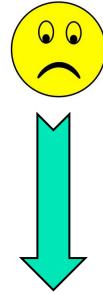
<sup>‡</sup>Florida International University

# NAND Flash Memory

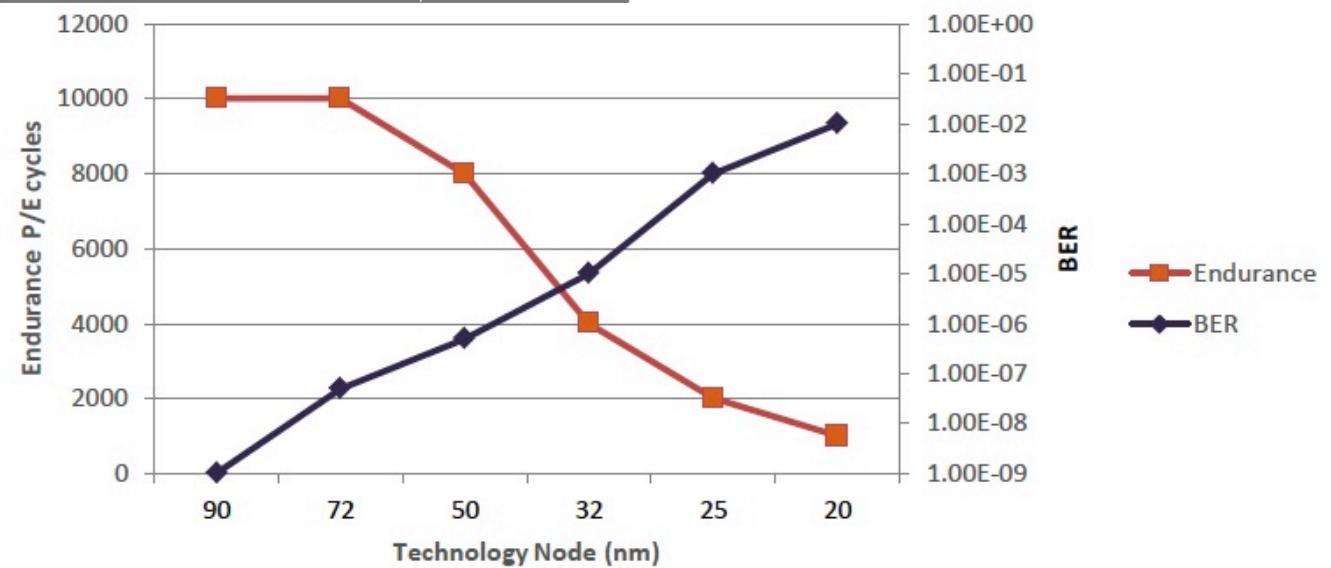
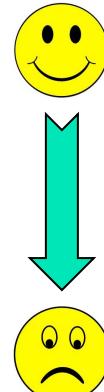


Bit cost reduction

Price/GB

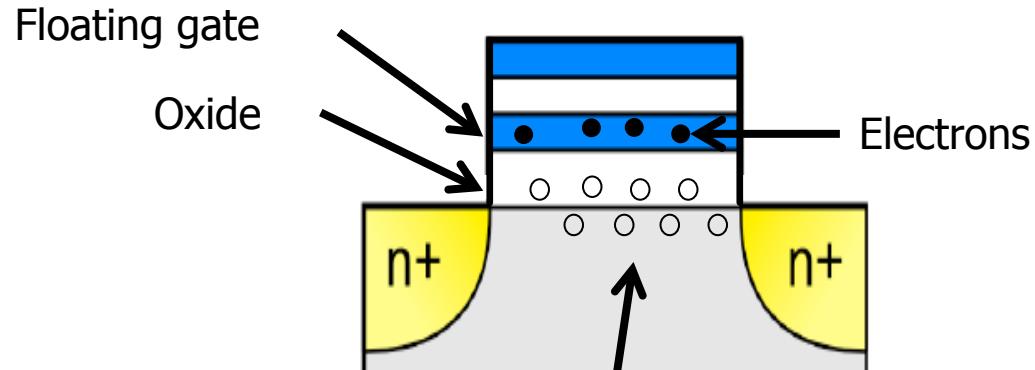


Lifetime



# Damage of NAND Flash memory cell

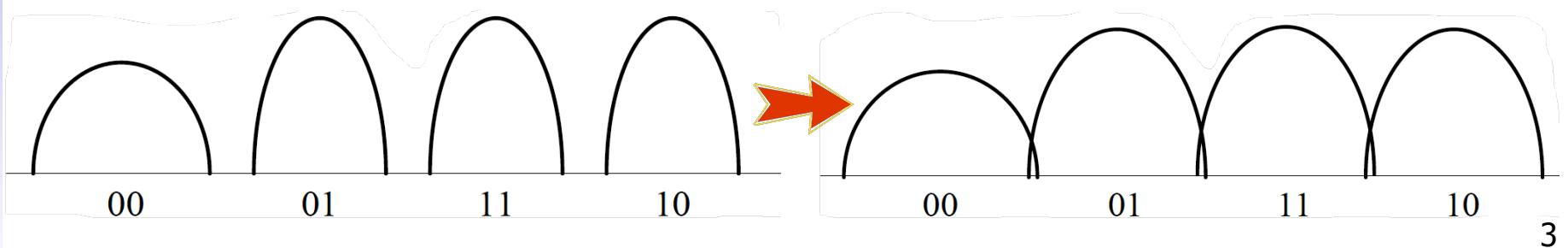
## □ Damage to the NAND Flash memory cell



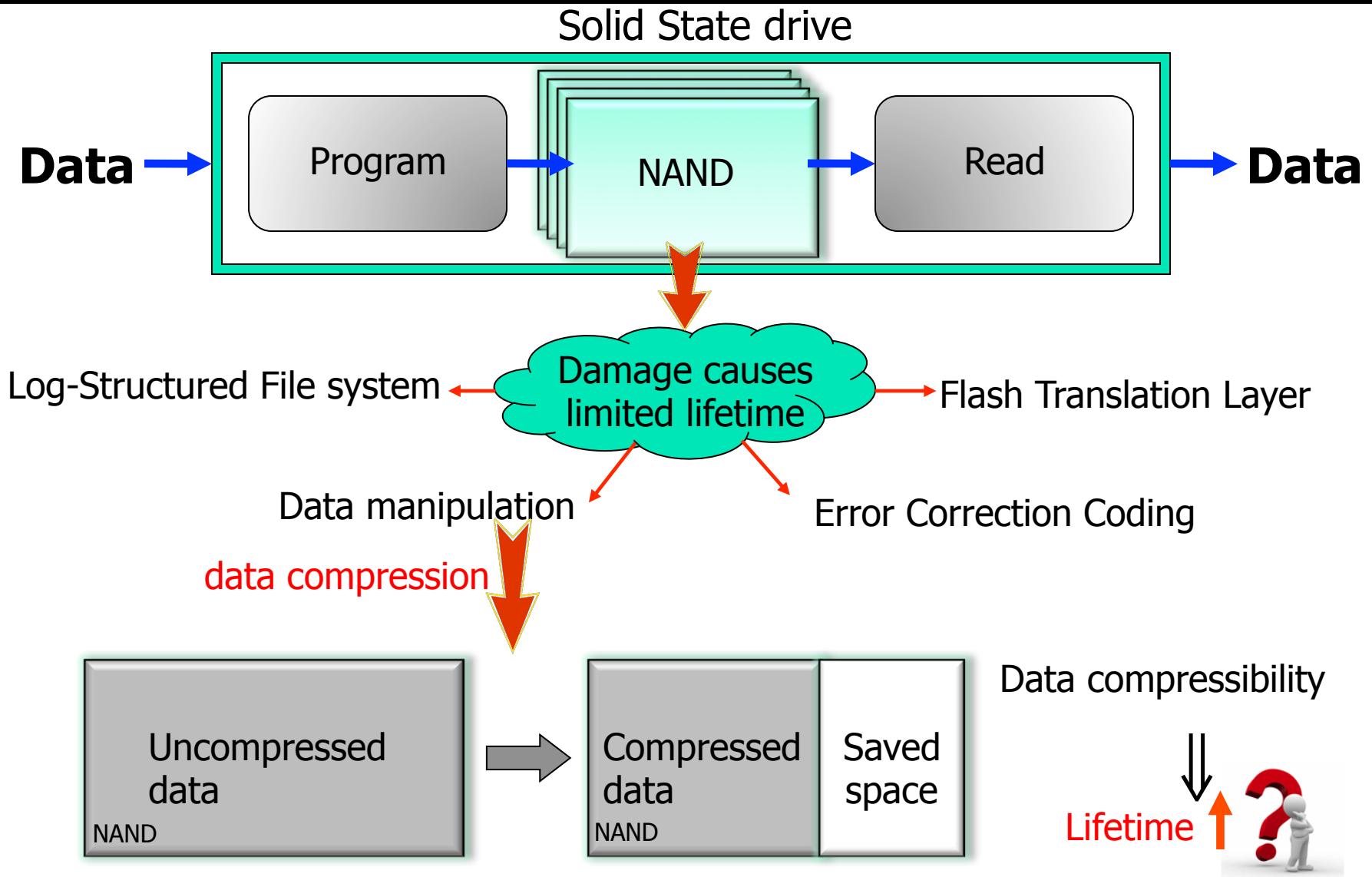
- Oxide layer becomes thinner
- Number of electrons held in floating gate is reduced

P/E cycling causes **Charge trap : Damage** to memory cell

## □ Threshold voltage distribution overlap



# Method to improve the lifetime

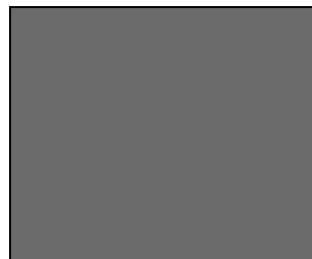


# Data compression in NAND Flash

Data compressibility :  $\alpha \Rightarrow$  Lifetime extends:  $1/\alpha$

- Unused space in one NAND Flash page

One sector data



data compression  
→



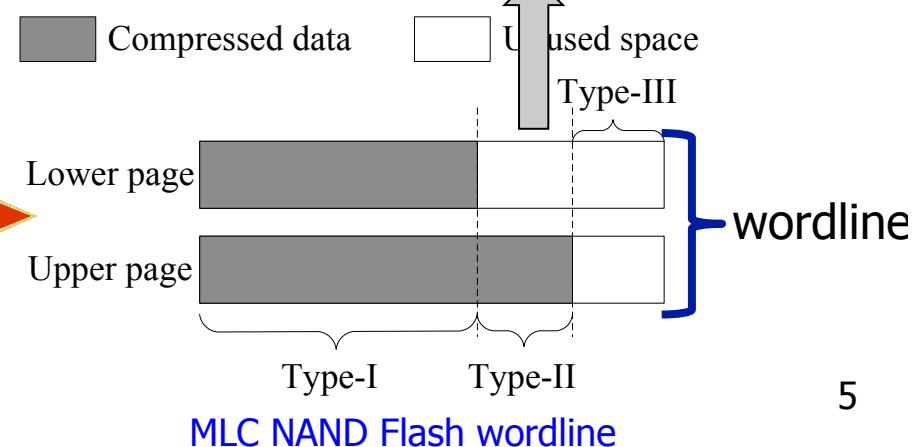
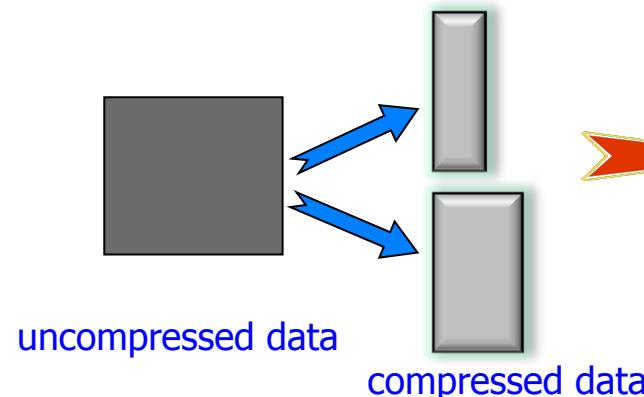
Physical NAND Flash page



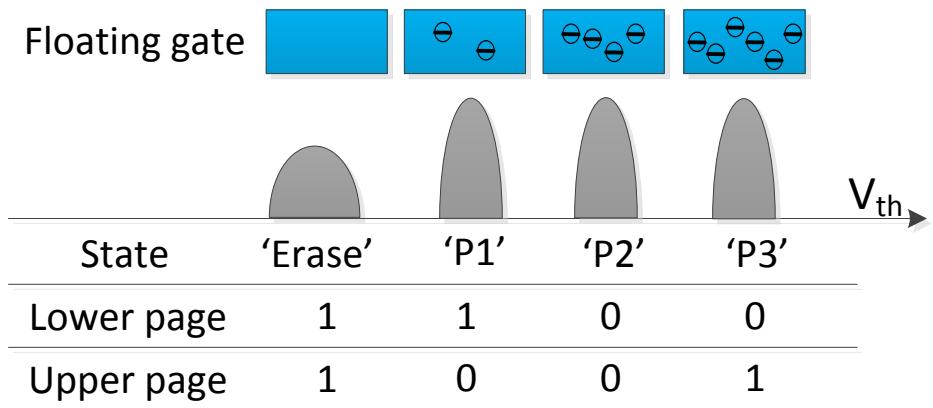
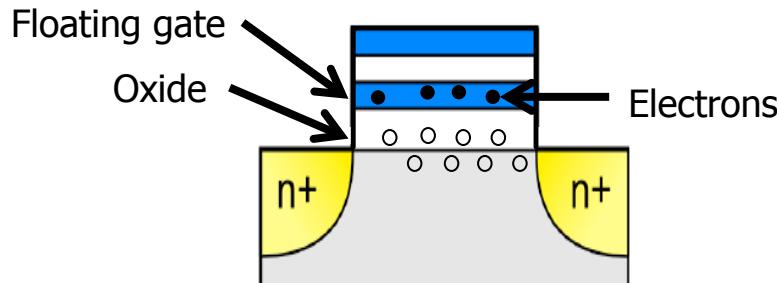
Unused space

Minimize{damage} ?

- Impact of compression ratio variance

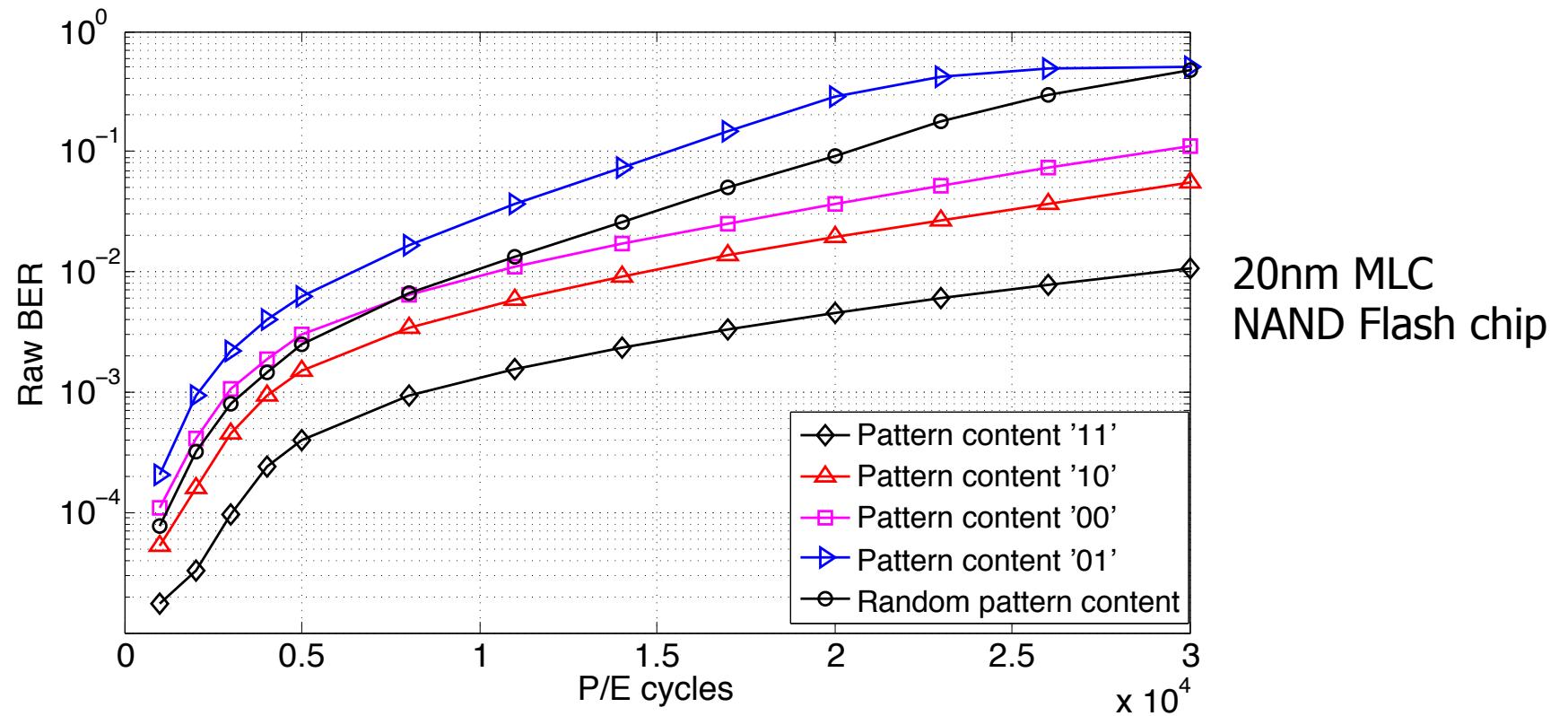


# Content-dependent damage characteristics

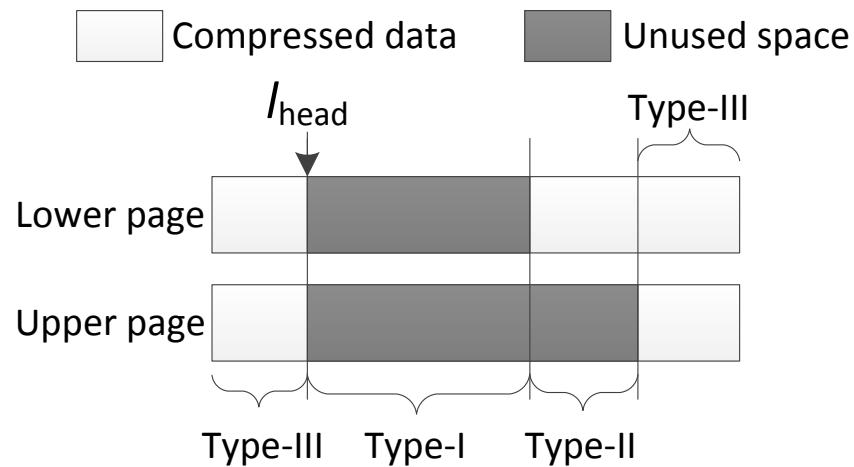


- Electrons quantity differentiate the damage of data patterns
- **NAND Flash memory experiences content-dependent memory damage**
- Damage of data pattern:  
pattern "11" < pattern "10" < pattern "00" < pattern "01"

# Content-dependent damage: test result



# Unused space filling strategies



Increase pattern "11" and "10";  
Decrease random data pattern and "01"

Unidirectional data layout (UD)

$S^{(l)}$ : Unused space in lower page  
 $S^{(u)}$ : Unused space in upper page

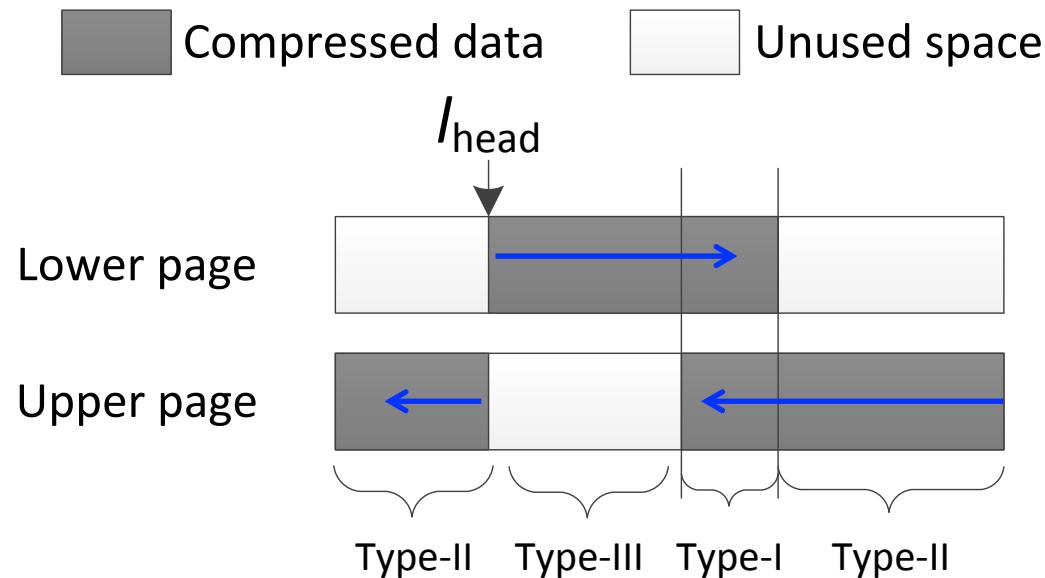
$b_l$ : lower page bit in memory cell k  
 $b_u$ : upper page bit in memory cell k

## Unused space filling rule:

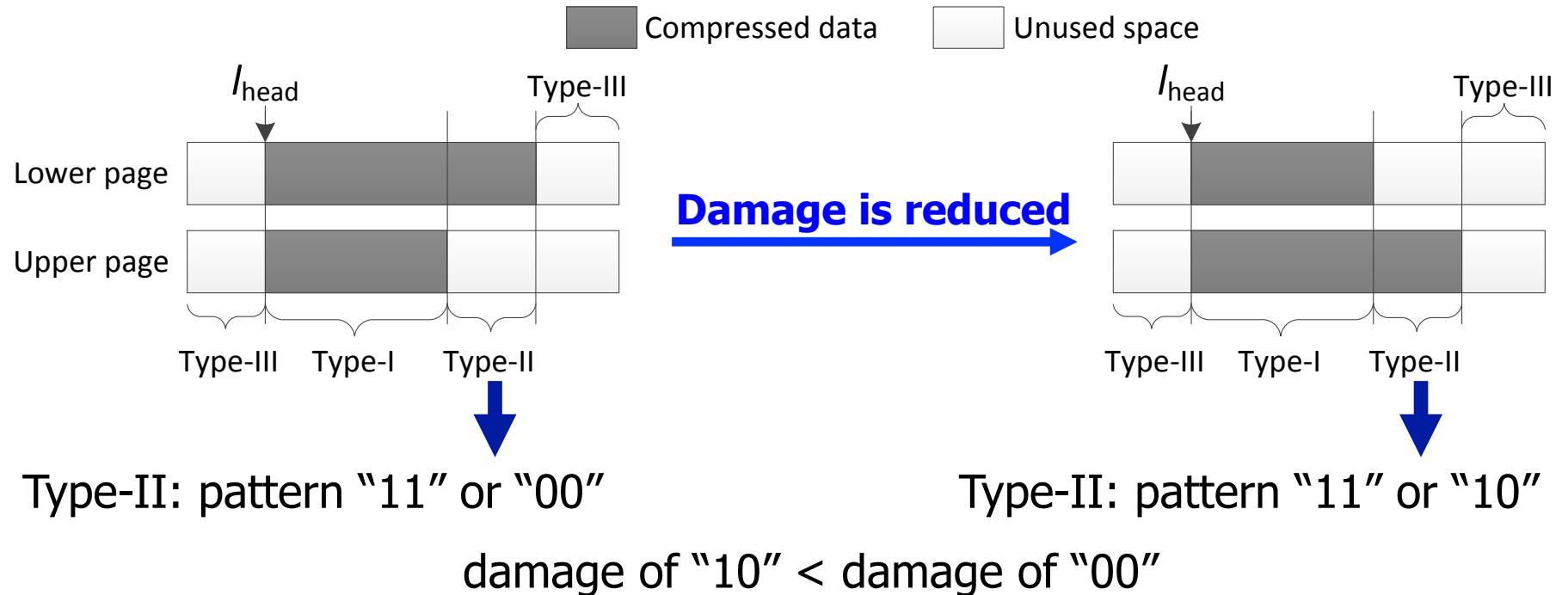
- If  $b_l \in S^{(l)}$  and  $b_u \in S^{(u)}$  (Type-III)  
Set  $b_l = b_u = 1$ ;
- If  $b_l \in S^{(l)}$  and  $b_u \notin S^{(u)}$  (Type-II-a)  
Set  $b_l = 1$  ;
- If  $b_l \notin S^{(l)}$  and  $b_u \in S^{(u)}$  (Type-II-b)  
Set  $b_l = b_u$ .

# Bidirectional data layout

- Bidirectional data layout (BD): To reduce the percentage of random data pattern (Type-I)



# Conditional data exchange



- ❑ Conditional data exchange: **exchange the compressed lower page data with upper page data to ensure the compressed lower page data has larger unused space**

May introduce extra overhead for FTL

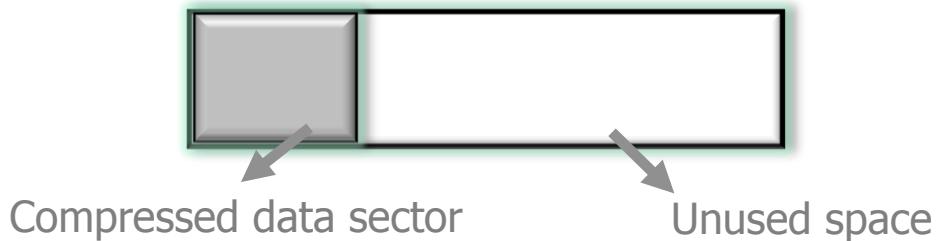
# Explicit compression and implicit compression

- Conventional compressed data storage : Explicit compression



- Complicate FTL/file system design

- Implicit compression : A transparent data compression stored method

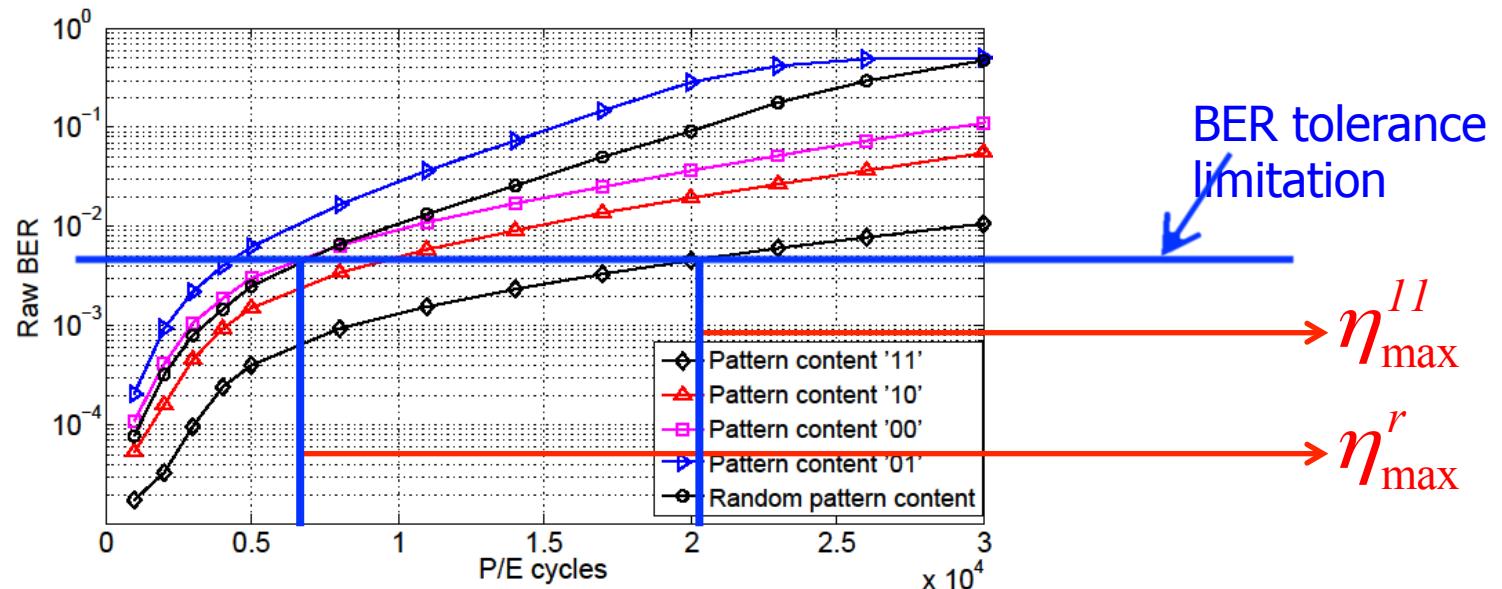


Compared with non-compression storage, the number of data sector in one Flash page is not increased

- Transparent to FTL and file system, simplify system design
  - Sacrifice data compressibility and damage reduction

# Damage factor of data pattern

## □ 20nm MLC NAND Flash test results



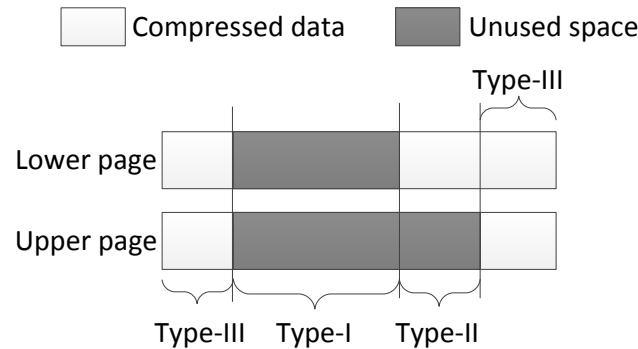
## □ Damage Factor $\rho_i$ : Measure the damage of data pattern $i$

$$\rho_i = \frac{\eta_{\max}^{(r)}}{\eta_{\max}^i}$$

# Mathematical model to evaluate Flash lifetime



Compressed data length in one page:  $C_S^{(e)}$



After  $t$  P/E cycles, NAND Flash memory device survival probability

Mathematical model

Block survival probability

: Model input      : Model output

Data compressibility (mean, variance)

Mathematical model

Distribution of  $C_S^{(e)}$

Damage factor of data patterns

Mathematical model

Distribution of memory cell damage per P/E

NAND Flash physical parameters

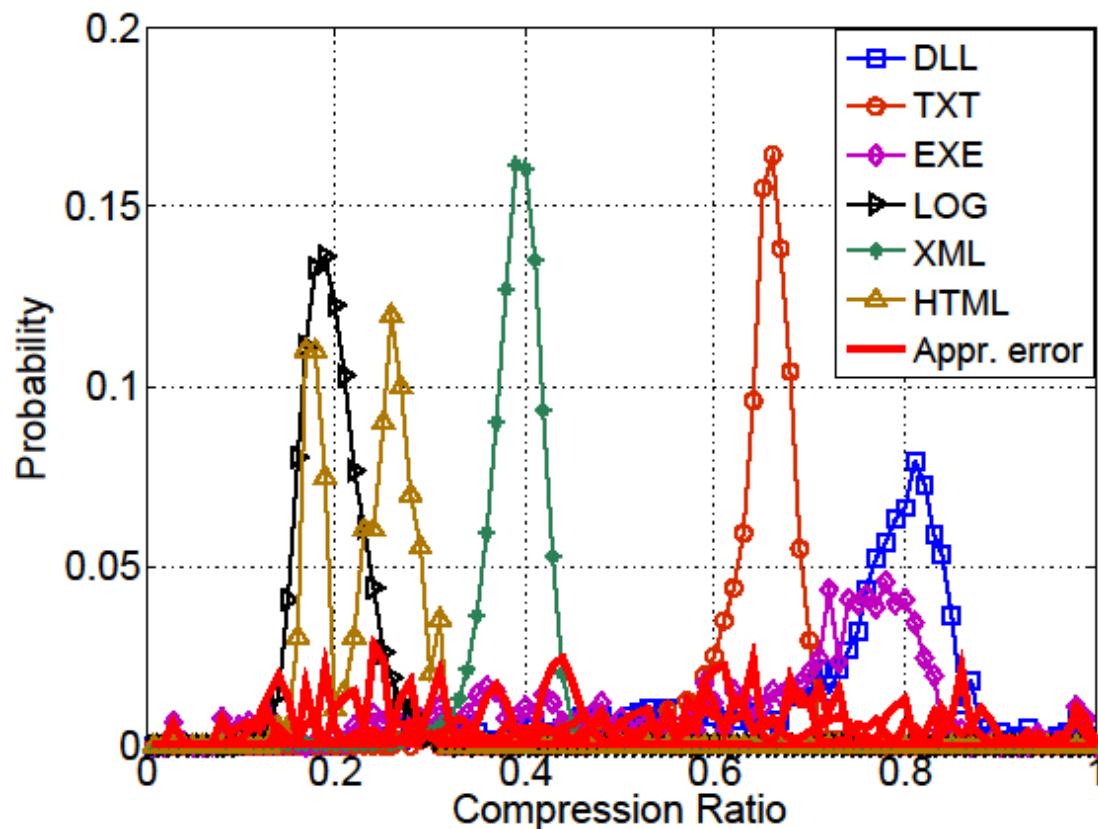
Mathematical model

Wordline survival probability

Mathematical model

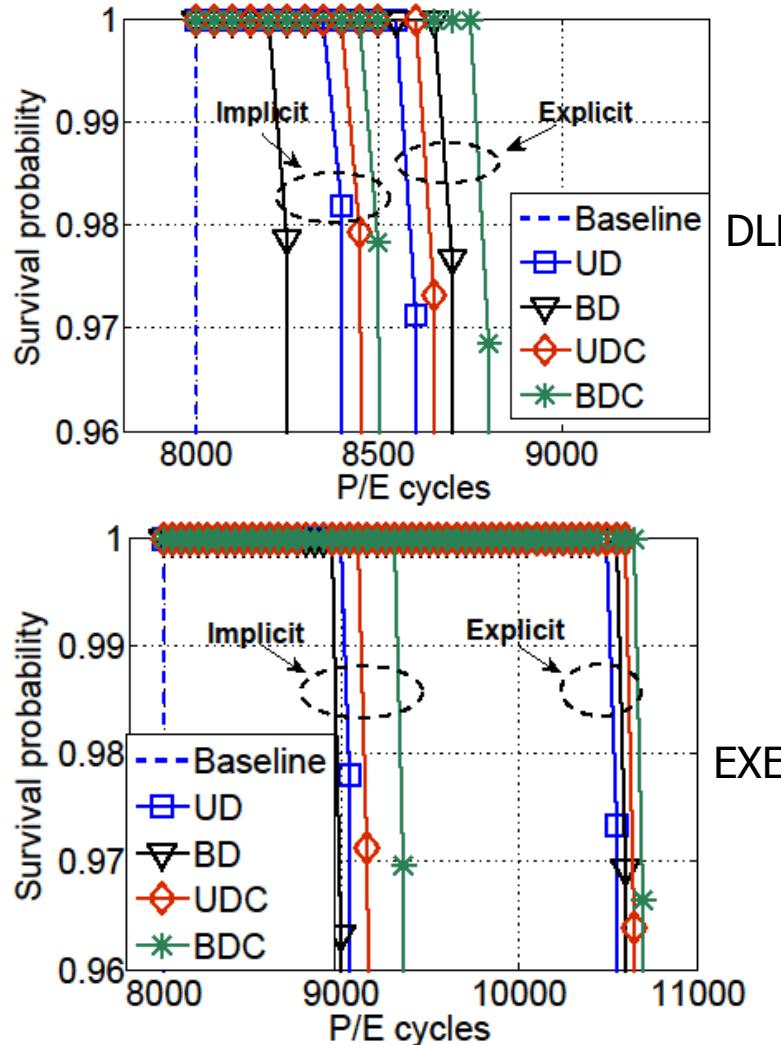
# Simulation results

- Selected data compressibility (LZ77 compression algorithm, 4kB data sector length)

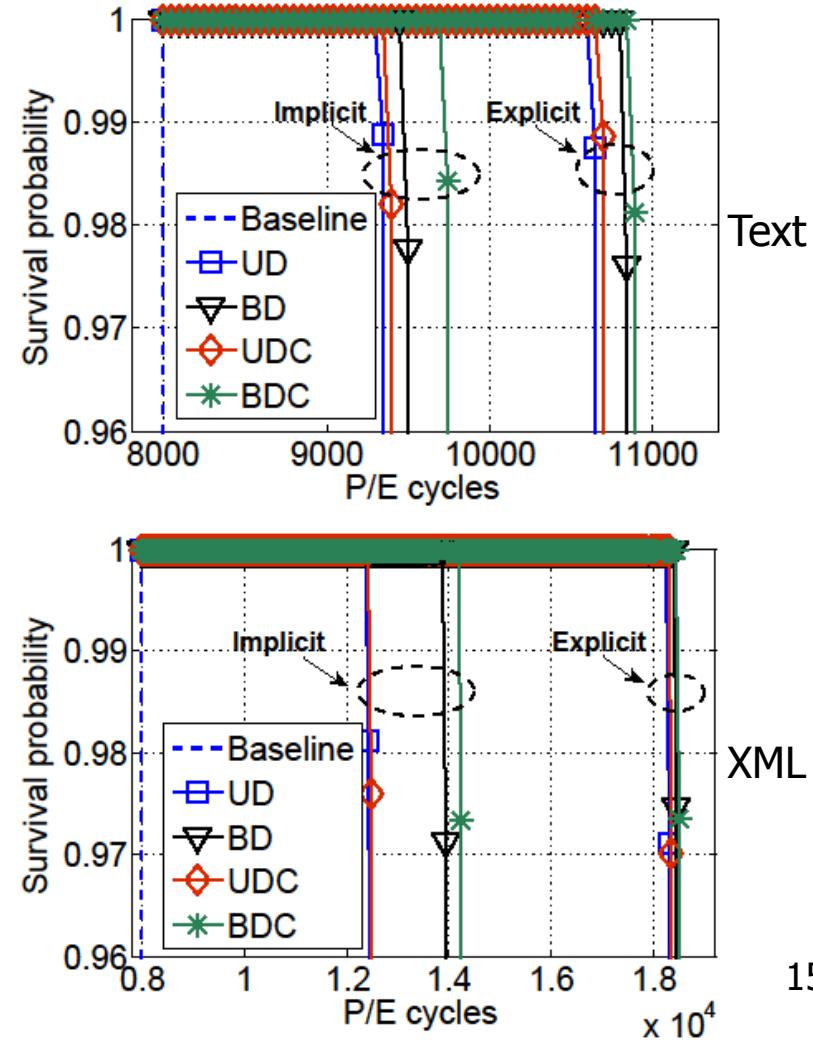


# Simulation results

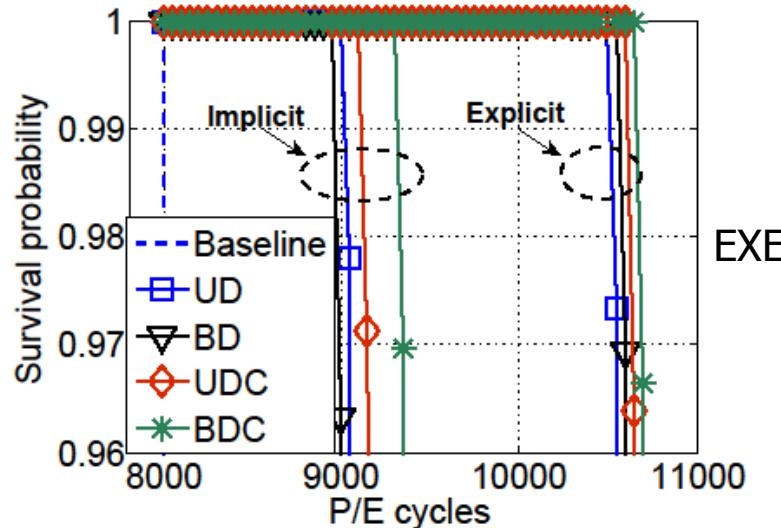
## □ Lifetime improvement by data compression storage techniques



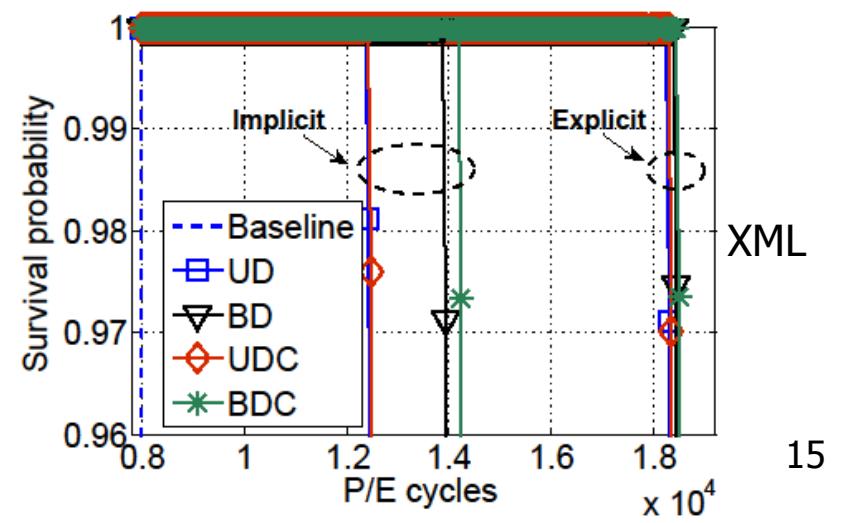
DLL



Text



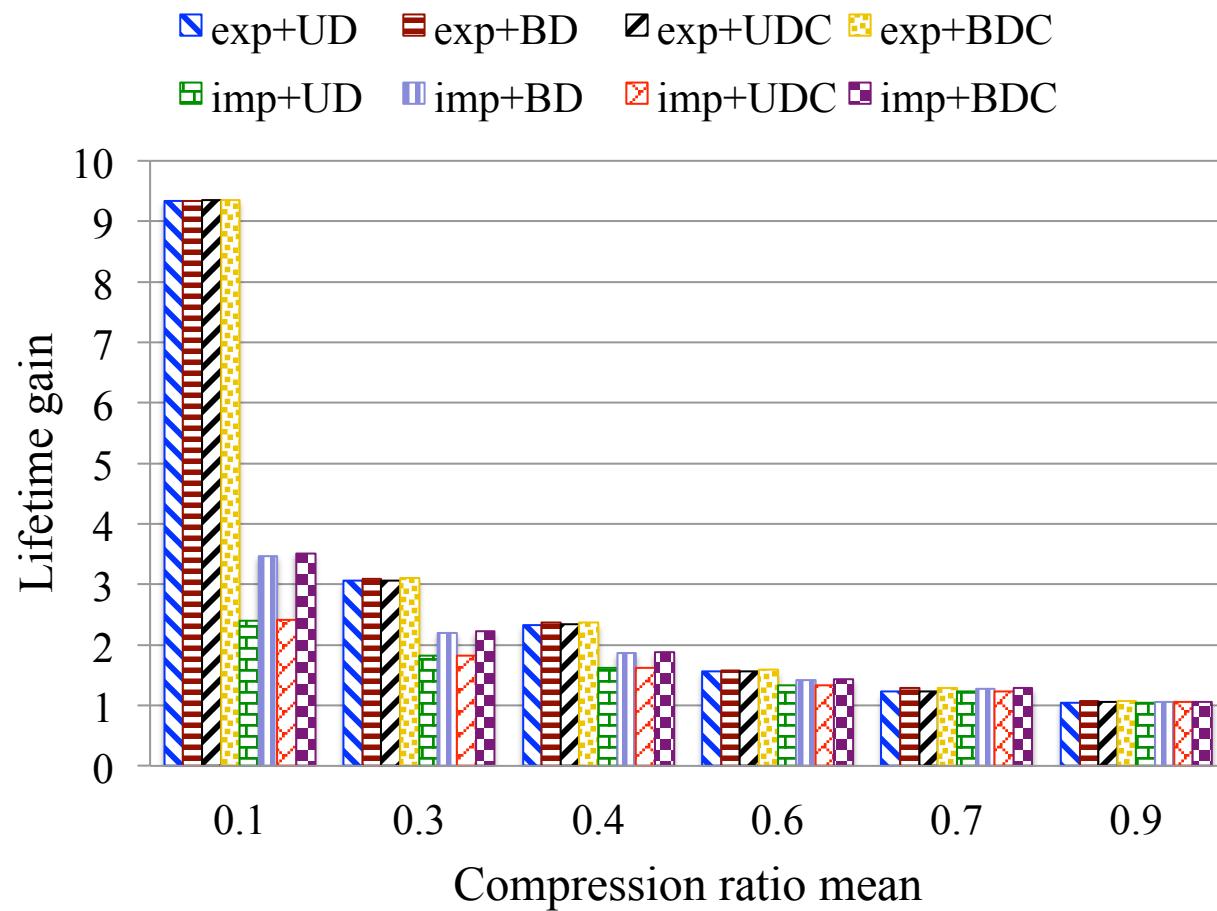
EXE



XML

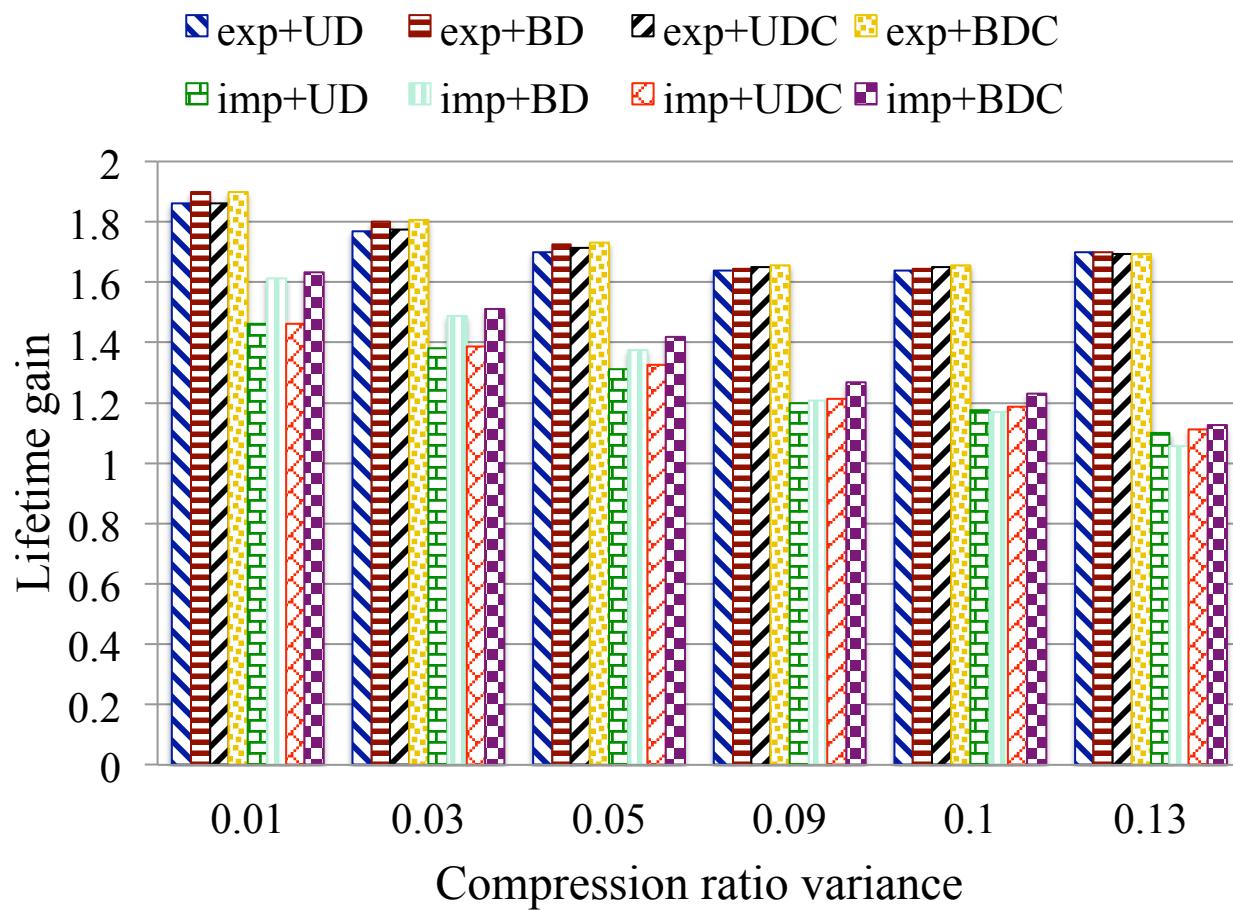
# Impact of data compression ratio mean

□ Compression ratio standard deviation fixes at 0.01



# Impact of data compression deviation

□ Compression ratio mean fixes at 0.5



# Conclusion

- Research on the employing data compressibility to reduce NAND Flash physical damage, in order to improve memory lifetime
  - Content-dependent damage feature of MLC NAND Flash to reduce damage from data program and erase.
  - A set of design strategies to exploit unused space from data compression in order to minimize the overall memory damage.
  - File system/FTL-friendly implicit compression as a complementary of conventional explicit compression.
  - Mathematical model to evaluate NAND Flash memory lifetime based on the data compressibility.